

## (Preliminary ver.) 1x4 25 Gbps 850 nm PIN Array (GSG)

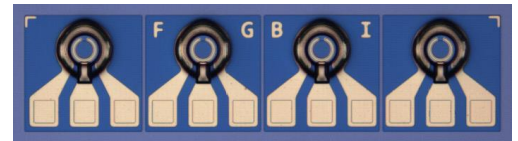
### L-CR-IM00-02

**Part Number: L-CR-IM00-02**

**Applications: 100 Gbps**

**Absolute Maximum Ratings (T = 25°C):**

Parameter	Symbol	Unit	Value
Forward Current	$I_F$	mA	10
Reverse Voltage	$V_R$	V	40
Reverse Current	$I_R$	mA	1
Operating Temperature	$T_{op}$	°C	0 - 90
Storage Temperature	$T_{stg}$	°C	-40 - 100



**Electro-optical Characteristics (T = 25°C, unless noted otherwise):**

Parameter	Symbol	Unit	Min.	Typ.	Max.	Test Condition
Aperture	D	μm		38		
Responsivity	R	A/W		0.5		$V_R = 5\text{ V}$ $\lambda = 850\text{ nm}$
Dark Current	$I_D$	nA		0.1	1.0	$V_R = 5\text{ V}$
Breakdown Voltage	$V_B$	V	50			$I_R = 1\text{ }\mu\text{A}$
Capacitance	C	pF		0.09	0.14	$V_R = 2\text{ V}$ $f = 1\text{ MHz}$
Peak Wavelength	$\lambda$	nm		850	860	

**Chip configuration:**

- Both anode and cathode contacts on top (epi) surface.
- Dimension: 290 (length) x 1050 μm (width) x 130 μm (thickness) with 250μm pitch  
Tolerance: +/-12.5μm  
Per channel dimension: 250 μm (width) x 290 μm (length)
- Bond pad size: 60 x 60 μm square
- P-bond pad in the middle